



PRELIMINARY

SOLID STATE DEVICES, INC

14849 Firestone Boulevard · La Mirada, CA 90638
Phone: (714) 670-SSDI (7734) · Fax: (714) 522-7424

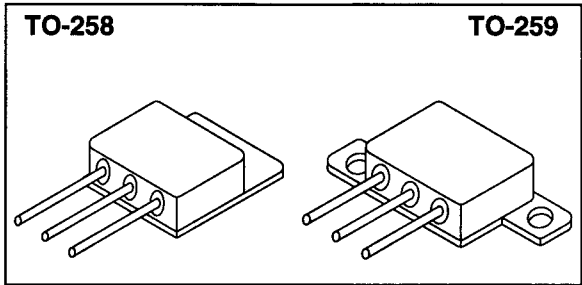
SFF24N50N SFF24N50P

Designer's Data Sheet

FEATURES:

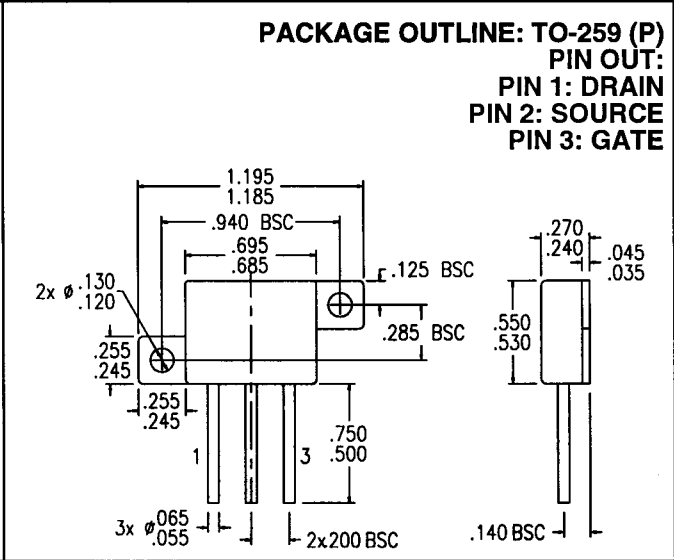
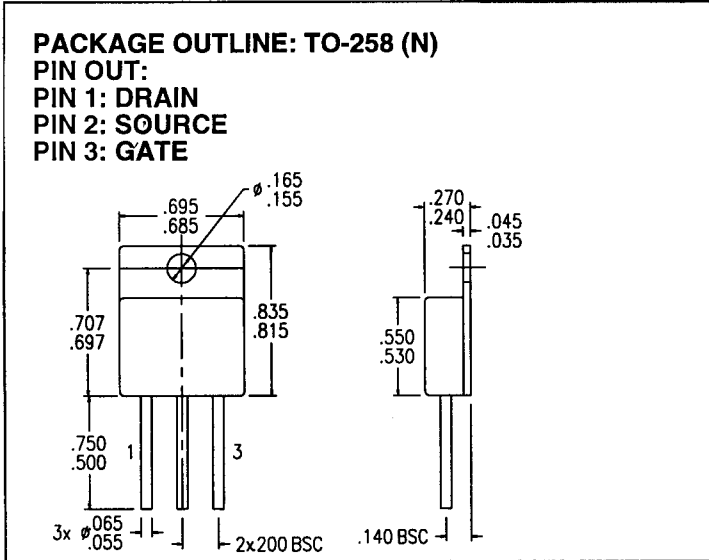
- Rugged construction with polysilicon gate
- Low RDS(on) and high transconductance
- Excellent high temperature stability
- Very fast switching speed
- Fast recovery and superior dv/dt performance
- Increased reverse energy capability
- Low input and transfer capacitance for easy paralleling
- Ceramic Seals for improved hermeticity
- Hermetically sealed surface mount power package
- TX, TXV and Space Level screening available
- Replaces: IXTH24N50 Types

24 AMP
500 VOLTS
0.23 Ω
N-CHANNEL
POWER MOSFET



MAXIMUM RATINGS

CHARACTERISTIC	SYMBOL	VALUE	UNIT
Drain to Source Voltage	V _{DS}	500	Volts
Gate to Source Voltage	V _{GS}	±20	Volts
Continuous Drain Current	I _D	24	Amps
Operating and Storage Temperature	T _{op} & T _{stg}	-55 to +150	°C
Thermal Resistance, Junction to Case	R _{θJC}	0.83	°C/W
Total Device Dissipation @ TC=25°C	P _D	150	Watts
Total Device Dissipation @ TC=55°C		114	



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: F00169 C

MED

SFF24N50N SFF24N50P

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ELECTRICAL CHARACTERISTICS @ T_J=25°C (Unless Otherwise Specified)

RATING		SYMBOL	MIN	TYP	MAX	UNIT
Drain to Source Breakdown Voltage (V _{GS} =0 V, I _D =250μA)		BV _{DSS}	500	---	---	V
Drain to Source on State Resistance (V _{GS} =10 V, I _D =50% Rated ID)		R _{DS(on)}	---	---	0.25	Ω
On State Drain Current (V _{DS} > I _{D(on)} X R _{DS(on)} Max, V _{GS} =10 V)		I _{D(on)}	24	---	---	A
Gate Threshold Voltage (V _{DS} ≥ V _{GS} , I _D =4mA)		V _{GS(th)}	2.0	---	4.0	V
Forward Transconductance (V _{DS} > I _{D(on)} X R _{DS(on)} Max, I _{DS} =50% rated ID)		g _{fs}	12	16	---	S(Ω)
Zero Gate Voltage Drain Current (V _{DS} =max rated voltage, V _{GS} =0 V) (V _{DS} =80% rated V _{DS} , V _{GS} =0 V, T _A =125°C)		I _{DSS}	---	---	250 1000	μA
Gate to Source Leakage Forward Gate to Source Leakage Reverse	At rated V _{GS}	I _{GSS}	---	---	+100 -100	nA
Total Gate Charge Gate to Source Charge Gate to Drain Charge	V _{GS} =10 Volts 50% rated V _{DS} 50% Rated ID	Q _g Q _{gs} Q _{gd}	---	135 28 62	180 40 85	nC
Turn on Delay Time Rise Time Turn Off Delay Time Fall Time	V _{DD} =50% rated V _{DS} 50% rated ID R _G =6.2Ω V _{GS} =10V	t _{d(on)} t _r t _{d(off)} t _f	---	16 33 65 30	30 45 130 40	nsec
Diode Forward Voltage (I _S =rated I _D , V _{GS} =0 V, T _J =25°C)		V _{SD}	---	---	1.5	V
Diode Reverse Recovery Time Reverse Recovery Charge	T _J =25°C I _F =10 A di/dt=100 A/μsec	t _{rr} Q _{RR}	---	---	500 ---	nsec μC
Input Capacitance Output Capacitance Reverse Transfer Capacitance	V _{GS} =0 Volts V _{DS} =25 Volts f = 1 MHz	C _{iss} C _{oss} C _{rss}	---	4200 450 135	---	pF

SAFE OPERATING AREA (S.O.A.)
T_C = 25°C, D.C. CONDITION

